

FEATURES

Complimentary to S8050

MARKING: 2TY

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-25	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	0.3	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to +150	℃

S8550 (PNP)



ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = -100\mu A, I_E = 0$	-40		V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1mA, I_B = 0$	-20		V
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100\mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -40V, I_E = 0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -20V, I_B = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1V, I_C = -50mA$	120	400	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -500mA$	5		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA$		-1.2	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -20mA$ $f = 30MHz$	150		MHz

CLASSIFICATION OF h_{FE}

Rank	L	H	
Range	120-200	200-350	

S8550 Typical Characteristics

